



LIGITEK ELECTRONICS CO.,LTD.
Property of Ligitek Only

NPN SILICON PHOTOTRANSISTOR LED LAMPS



Lead-Free Parts

LPT3333/A-PF

DATA SHEET

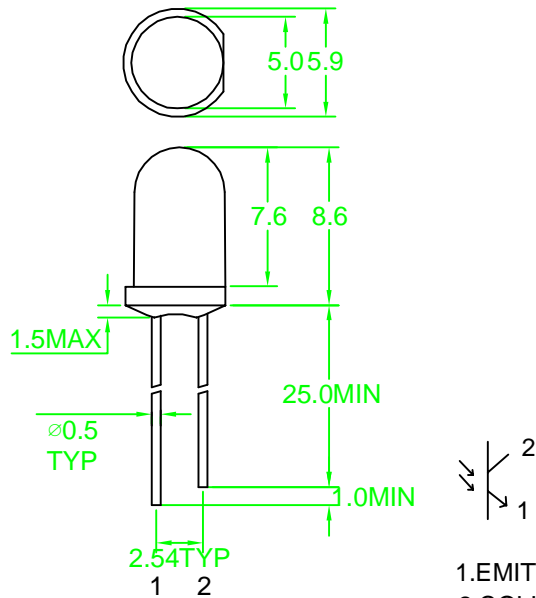
DOC. NO : QW0905-LPT3333/A-PFA

REV. : A

DATE : 12-Dec.-2018



Package Dimension



Features

- . High illumination sensitivity
- . Stable characteristics
- . Spectrally and mechanically matched with IR emitter

Description

The LPT3333/A-PF series are silicon nitride passivated NPN planar phototransistors with exceptionally stable characteristics and high illumination sensitivity the cases of LPT3333/A-PF are encapsulated in water clear plastic T1 3/4 package individualt

Note:1.All dimension are in millimeter tolerance is $\pm 0.25\text{mm}$ unless otherwise noted
2.Specifications are subject to change without notice

• MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

PARAMETER	MAXIMUM RATINGS	UNIT
Power Dissipation	100	mw
Collector-Emitter Voltage	30	V
Emitter-Collector Voltage	5	V
Electrostatic Discharge	8000	V
Operating Temperature	-50°C TO +100°C	
Storage Temperature	-50°C TO +100°C	

• ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$)

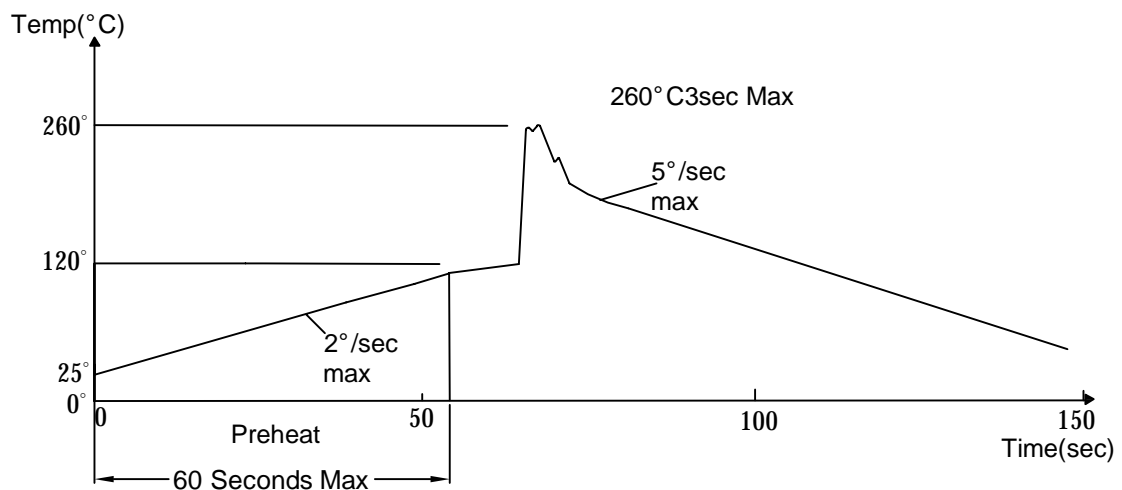
PARAMETER	SYMBOL	Min.	Typ.	Max.	UNIT	TEST CONDITION
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	$I_c=0.5\text{mA}$ $E_e=0\text{mw/cm}^2$
Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	5			V	$I_E=100\ \mu\text{A}$ $E_e=0\text{mw/cm}^2$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.12	V	$I_c=0.5\text{mA}$ $E_e=20\text{mw/cm}^2$
Rise Time	T_r		5		μs	$V_{CE}=30\text{V}$ $I_C=800\ \mu\text{A}, R_L=1\text{K}\ \Omega$
Fall Time	T_f		5		μs	
Collector Dark Current	I_{CEO}			100	nA	$V_{CE}=10\text{V}$ $E_e=0\text{mw/cm}^2$
On State Collector Current	$I_{p(on)}$	2.0		4.0	mA	$V_{CE}=5\text{v}$ $E_e=1\text{mw/cm}^2$ $\lambda P=940\text{nm}$
		4.0		8.0	mA	
		8.0		16.0	mA	
		16.0			mA	

Soldering Condition(Pb-Free)**1.Iron:**

Soldering Iron:30W Max
Temperature 350° C Max
Soldering Time:3 Seconds Max(One time only)
Distance:2mm Min(From solder joint to body)

2.Wave Soldering Profile

Dip Soldering
Preheat: 120° C Max
Preheat time: 60seconds Max
Ramp-up
2° C/sec(max)
Ramp-Down:-5° C/sec(max)
Solder Bath:260° C Max
Dipping Time:3 seconds Max
Distance:2mm Min(From solder joint to body)



Note: 1.Wave solder should not be made more than one time.
2.You can just only select one of the soldering conditions as above.

Reliability Test:

Test Item	Test Condition	Description	Reference Standard
Operating Life Test	1.Under Room Temperature 2.If=20mA 3.t=1000 hrs (-24hrs, +72hrs)	This test is conducted for the purpose of determining the resistance of a part in electrical and thermal stressed.	MIL-STD-750: 1026 MIL-STD-883: 1005 JIS C 7021: B-1
High Temperature Storage Test	1.Ta=85°C±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of high temperature for hours.	MIL-STD-883:1008 JIS C 7021: B-10
Low Temperature Storage Test	1.Ta=-40°C±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of low temperature for hours.	JIS C 7021: B-12
High Temperature High Humidity Test	1.Ta=65°C±5°C 2.RH=90%~95% 3.t=240hrs±2hrs	The purpose of this test is the resistance of the device under tropical for hours.	MIL-STD-202:103B JIS C 7021: B-11
Thermal Shock Test	1.Ta=105°C±5°C & -40°C±5°C (10min) (10min) 2.total 10 cycles	The purpose of this is the resistance of the device to sudden extreme changes in high and low temperature.	MIL-STD-202: 107D MIL-STD-750: 1051 MIL-STD-883: 1011
Solder Resistance Test	1.T.Sol=260°C±5°C 2.Dwell time= 10±1sec.	This test intended to determine the thermal characteristic resistance of the device to sudden exposures at extreme changes in temperature when soldering the lead wire.	MIL-STD-202: 210A MIL-STD-750: 2031 JIS C 7021: A-1
Solderability Test	1.T.Sol=230°C±5°C 2.Dwell time=5±1sec	This test intended to see soldering well performed or not.	MIL-STD-202: 208D MIL-STD-750: 2026 MIL-STD-883: 2003 JIS C 7021: A-2